

# 1SS388

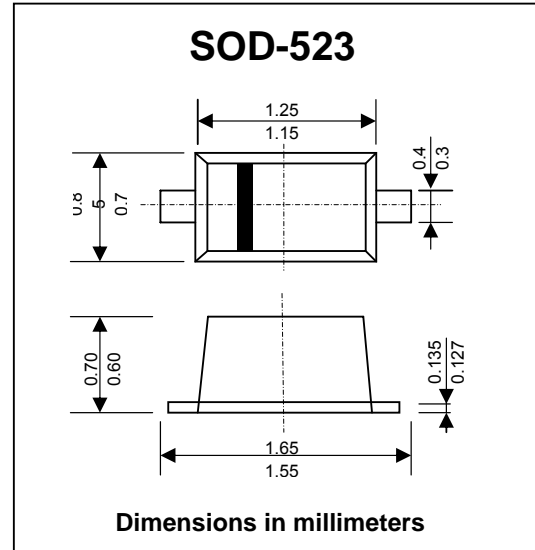
## SILICON EPITAXIAL SCHOTTKY BARRIER DIODE

### FEATURES :

- \* Small package
- \* Low forward voltage
- \* Low reverse current
- \* Pb / RoHS Free

### MECHANICAL DATA :

- \* Lead Finish : 100% Matte Sn (Tin)
- \* Mounting Position : Any
- \* Qualified Max Reflow Temperature : 260 °C



### Absolute Maximum Ratings (Ta = 25 °C)

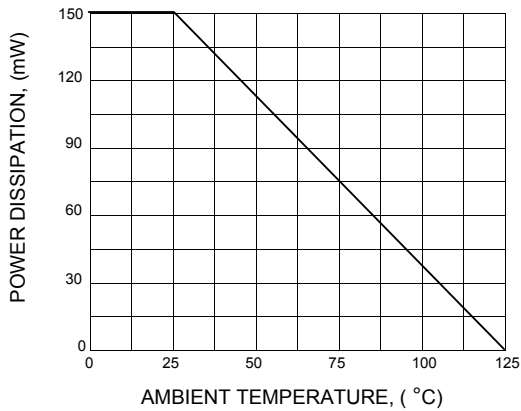
Parameter	Symbol	Value	Unit
Maximum Peak Reverse Voltage	$V_{RM}$	45	V
Maximum Reverse Voltage	$V_R$	40	V
Maximum Average Forward Current	$I_F$	100	mA
Maximum Peak Forward Current	$I_{FM}$	300	mA
Maximum Surge Current (10 ms)	$I_{FSM}$	1.0	A
Power Dissipation	$P_{tot}$	150	mW
Junction Temperature	$T_J$	125	°C
Storage Temperature Range	$T_{STG}$	-55 to + 125	°C

### Electrical Characteristics (Ta = 25 °C)

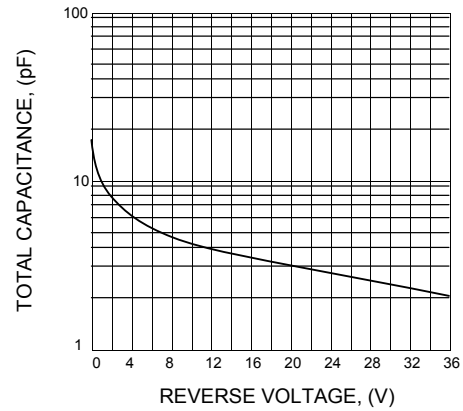
Parameter	Symbol	Test Condition	Max.	Unit
Forward Voltage	$V_F$	$I_F = 50 \text{ mA}$	0.6	V
Reverse Current	$I_R$	$V_R = 10 \text{ V}$	5	$\mu\text{A}$
Total Capacitance	$C_T$	$f = 1\text{MHz}$	25	pF

### RATING AND CHARACTERISTIC CURVES ( 1SS388 )

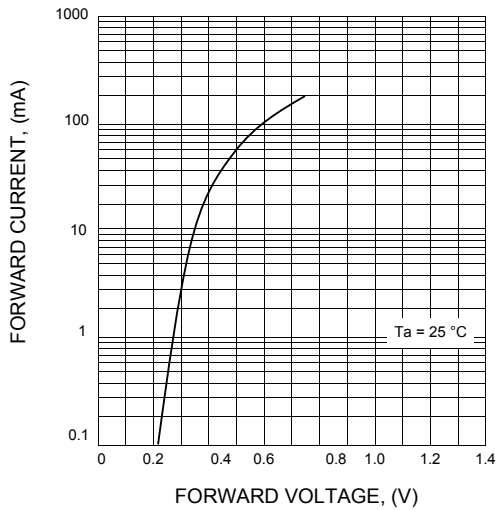
**FIG.1 - POWER DISSIPATION VS. AMBIENT TEMPERATURE**



**FIG.2 - TOTAL CAPACITANCE VS. REVERSE VOLTAGE**



**FIG.3 - TYPICAL FORWARD CHARACTERISTICS**



**FIG.4 - TYPICAL REVERSE CHARACTERISTICS**

